



**UNIVERSITI PUTRA MALAYSIA**

**MAGNETIC PROPERTIES OF RF MAGNETRON SPUTTERED Co-Ag-Cu  
GRANULAR THIN FILMS**

**KABASHI KHATIR KABASHI**

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**MAGNETIC PROPERTIES OF RF MAGNETRON SPUTTERED Co-Ag-Cu  
GRANULAR THIN FILMS**

By

**KABASHI KHATIR KABASHI**

**Thesis Submitted in Fulfilment of the Requirements for the Degree of Master of  
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**June 2000**



## ***DEDICATION***

***Special Dedication is due to:***

***Dr. Joshua Otor Akol (Deputy Vice Chancellor Upper Nile University)***

***My Late Father, Mother, Brothers and Sisters***

***My Wife and my Sons***



Abstract of thesis presented to the Senate of Universiti Putra Malaysia in fulfilment of the requirements for the degree of Master of Science

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**KABSAHI KHATIR KABASHI**

**June 2000**

**Chairman: Professor Abdul Halim Shaari, Ph. D.**

**Faculty: Science and Environmental Studies**

The observation of the magnetoresistance (MR) effect in granular films, where the magnetic particles are embedded in a non-magnetic matrix, has stimulated remarkable interest because of its potential technological applications as magnetic sensors in the magnetic storage technology, and also due to interest in fundamental scientific research. The granular films can present MR effect even larger than in multilayers. The MR effect was a large decrease in electrical resistivity that occurs when the magnetization of two layered or granular samples was aligned by an external magnetic field. In surface morphology was smooth and homogeneous and there was a little contamination on these surfaces as indicated through SEM, which may be attributed to the oil spots and fingerprints throughout the deposition process and preparation for various measurements. The chemical composition and the element percentage for each series were determined by EDX.

The structure of the samples was characterized by XRD. The peaks of fcc (111), (200), (220), and (311) related to the Ag were detected and a set of fcc (111) and (220) peaks related to the Co were detected as well, indicating the formation of small fcc Co particles in Ag. The XRD measurements also detected the peak of fcc (111) related to the Cu and Co. However, the other peaks of fcc Cu (+Co) (200) and fcc Cu (+Co) (220) were not detected. Ag (111) peak shifts to higher angles ( $2\theta > 38.11$ ) for the samples of  $\text{Co}_{0.53}\text{Ag}_{0.47}$ ,  $\text{Co}_{0.23}\text{Cu}_{0.77}$ , and  $\text{Co}_{0.32}\text{Ag}_{0.14}\text{Cu}_{0.54}$ , while for the  $\text{Co}_{0.26}\text{Ag}_{0.19}\text{Cu}_{0.55}$  and  $\text{Co}_{0.30}\text{Ag}_{0.46}\text{Cu}_{0.24}$  samples the peak shifts to lower angles ( $2\theta < 38.11$ ).

The as-deposited samples measurements at room temperature displayed a maximum value of 1.26% MR obtained by the  $\text{Co}_{0.32}\text{Ag}_{0.14}\text{Cu}_{0.54}$  film when the deposition time was 80 minutes. The remaining samples of  $\text{Co}_{0.23}\text{Cu}_{0.77}$ ,  $\text{Co}_{0.26}\text{Ag}_{0.19}\text{Cu}_{0.55}$ ,  $\text{Co}_{0.30}\text{Ag}_{0.46}\text{Cu}_{0.24}$ , and  $\text{Co}_{0.55}\text{Ag}_{0.47}$  have shown the values of 0.13%, 0.24%, 0.36%, and 0.84% MR respectively for the deposition time of 90 minutes. Post-annealing increased the MR for all the samples at room temperature and at low temperatures. The measurements of annealed samples at room temperature exhibited the values of 1.75%, 1.28%, 0.52%, 0.31%, and 0.  $\text{Co}_{0.32}\text{Ag}_{0.14}\text{Cu}_{0.54}$ ,  $\text{Co}_{0.53}\text{Ag}_{0.47}$ ,  $\text{Co}_{0.30}\text{Ag}_{0.46}\text{Cu}_{0.24}$ ,  $\text{Co}_{0.26}\text{Ag}_{0.19}\text{Cu}_{0.55}$ , and  $\text{Co}_{0.23}\text{Cu}_{0.77}$  respectively of the samples deposited for 90 minutes. The increase in the MR due to annealing process may be related to the reducing of the degree of structural disorder, enlarging the particle size and increasing of the interparticle separation, which may affect to the effect of phonon behavior on the resistivity of the film.

Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia sebagai memenuhi keperluan untuk ijazah Master Sains

## **KAJIAN MAGNETORINTANGAN SAPUT TIPIS GRANULAR**

**Oleh**

**KABASHI KHATIR KABASHI**

**Jun 2000**

**Pengerusi: Profesor Abdul Halim Shaari, Ph. D**

**Fakulti: Sains dan Pengajian Alam Sekitar**

Pencerapan kesan magnetorintangan dalam filem granular dimana bahan magnet telah dibentuk oleh zarah magnet yang dibenamkan didalam bahan bukan magnet, telah merangsang aktiviti yang tinggi disebabkan oleh potensi kegunaan teknologinya sebagai sensor magnet dalam teknologi pengstoran magnet, dan juga keistimewaan dalam penyelidikan saintifik asasnya. Filem granular boleh memperolehi kesan magnetorintangan yang lebih besar dari filem multilapisan. Tetapi, magnetorintangan adalah satu peningkatan yang besar dalam rintangan elektrik dimana ia berlaku bila keadaan magnet bagi dua lapisan atau granular sampel telah disusun oleh satu medan magnet luaran.

Dalam kajian ini, telah diperhatikan bahawa morforlogi permukaan adalah rata dan homogen dan juga terdapat sedikit pencemaran berlaku pada permukaan yang dapat diperhatikan dari imbasan elektron mikroskop (SEM), dimana ia mungkin disebabkan oleh kesan minyak dan cap jari dalam seluruh proses pemendapan dan juga penyediaan bagi pengukuran yang berbeza. Komposisi bahan kimia dan peratusan bahan bagi setiap siri telah ditentukan oleh analisis penyebaran sinaran-X (EDX).

Struktur bagi sampel telah dianalisiskan oleh pembelauan sinaran-X (XRD) Puncak fcc (111), (200), (220) dan (311) yang berkaitan dengan bahan Ag telah dikesan dan satu set puncak fcc(111) dan (220) yang menunjukkan bahan Co telah terhasil, termasuk pembentukan hablur fcc (111) Co yang kecil dalam Ag Pengukuran XRD juga dapat kesan puncak fcc (111) yang berkaitan dengan Cu dan Co Manakala, puncak lain seperti fcc Cu (+Co)(200) dan fcc Cu (+Co)(220) tidak dapat dikesan

Puncak Ag (111) beralih ke sudut yang lebih tinggi ( $2\theta > 38^{\circ} 11'$ ) bagi sampel  $\text{Co}_{0.53}\text{Ag}_{0.47}$ ,  $\text{Co}_{0.23}\text{Cu}_{0.77}$  dan  $\text{Co}_{0.32}\text{Ag}_{0.14}\text{Cu}_{0.54}$  manakala bagi sampel  $\text{Co}_{0.26}\text{Ag}_{0.19}\text{Cu}_{0.55}$  dan  $\text{Co}_{0.30}\text{Ag}_{0.46}\text{Cu}_{0.24}$  ia beralih ke sudut yang lebih rendah ( $2\theta < 38^{\circ} 11'$ )

Pengukuran sampel baru dipercik dalam suhu bilik menunjukkan satu nilai maksimum iaitu 1 26% bagi filem  $\text{Co}_{0.32}\text{Ag}_{0.14}\text{Cu}_{0.54}$  yang dipercik selama 80 minit Bagi sampel lain iaitu  $\text{Co}_{0.23}\text{Cu}_{0.77}$ ,  $\text{Co}_{0.26}\text{Ag}_{0.19}\text{Cu}_{0.55}$ ,  $\text{Co}_{0.3}$  dan  $\text{Co}_{0.53}\text{Ag}_{0.47}$  memberi nilai 0 13%, 0 24%, 0 36% dan 0 84% MR bagi pecikan masa selama 90 minit Pemanasan selepas penyediaan menambah nilai MR bagi semua sampel pada suhu bilik dan suhu rendah Pengukuran bagi sampel, yang telah sepuhlindap, pada suhu bilik memberi nilai MR sebanyak 1 75%, 1 28%, 0 52%, 0 31% dan 0 16% bagi sampel  $\text{Co}_{0.32}\text{Ag}_{0.14}\text{Cu}_{0.54}$ ,  $\text{Co}_{0.53}\text{Ag}_{0.47}$ ,  $\text{Co}_{0.30}\text{Ag}_{0.46}\text{Cu}_{0.24}$ ,  $\text{Co}_{0.23}\text{Cu}_{0.77}$ ,  $\text{Co}_{0.26}\text{Ag}_{0.19}\text{Cu}_{0.55}$ ,  $\text{Co}_{0.3}$ ,  $\text{Co}_{0.53}\text{Ag}_{0.47}$  dan  $\text{Co}_{0.30}\text{Ag}_{0.46}\text{Cu}_{0.24}$ . Penambahan dalam nilai MR yang disebabkan oleh proses sepuhlindapan mungkin dihubungkaitkan dengan darjah ketidaksusunan struktur, pembesaran saiz hablur dan penambahan jarak antara hablur, merangsang kesan kelakuan fonon dalam kerintangan bagi filem

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I certify that an Examination Committee met on 29 June, 2000 to conduct the final examination of Kabashi Khatir Kabashi on his Master of Science thesis entitled "Magnetic Properties of RF Magnetron Sputtered Co-Ag-Cu Granular Thin Films" in accordance with Universiti Pertanian Malaysia (Higher Degree) Act 1980 and Universiti Pertanian Malaysia (Higher Degree) Regulations 1981. The Committee recommends that the candidate be awarded the relevant degree. Members of the Examination Committee are as follows:

**JAMIL SURADI, Ph.D.**

Faculty of Science and Environmental Studies  
Universiti Putra Malaysia  
(Chairman)

**ABDUL HALIM SHAARI, Ph. D.**

Professor  
Faculty of Science and Environmental Studies  
Universiti Putra Malaysia  
(Member)

**ZAINUL ABIDIN HASSAN, Ph.D.**

Faculty of Science and Environmental Studies  
Universiti Putra Malaysia  
(Member)

**W. MAHMOOD MAT YUNUS, Ph. D.**

Associate Professor  
Faculty of Science and Environmental Studies  
Universiti Putra Malaysia  
(Member)



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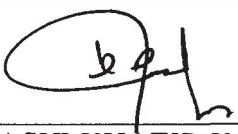
**MOHD. GHAZALI MOHAYIDIN, Ph.D.**  
Professor/Deputy Dean of Graduate School,  
Universiti Putra Malaysia  
Date:

**07 JUL 2000**

This thesis was submitted to the Senate of Universiti Putra Malaysia and was accepted as fulfilment of the requirements for the degree of Master of Science

*Kamis Awang*  
KAMIS AWANG, Ph. D.  
Associate Professor  
Dean of Graduate School  
Universiti Putra Malaysia  
Date: **13 JUL 2000**

I hereby declare that the thesis is based on my original work except for quotations and citations, which have been duly acknowledged I also declare that it has not been previously or concurrently submitted for any other degree at UPM or other institutions

  
KABASHI KHATIR KABASHI  
Date 6/7/2000

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## LIST OF ABBREVIATIONS AND GLOSSARY OF TERMS

Abbrev/Gloss	Description
$\alpha, \beta, \gamma$	Phase designations
$\theta$	Bragg diffraction angle
$\rho_{\uparrow}$	Spin-up density
$\rho_{\downarrow}$	Spin-down density
$\rho_F$	Ferromagnetic resistivity
$\rho_N$	Non ferromagnetic resistivity
$\rho_{\parallel}$	Parallel resistivity
$\rho_T$	Transverse resistivity
$\rho_b$	Bulk resistivity
$\rho_0$	Resistivity due to impurity
$\rho_H$	Resistivity at applied magnetic field H
$\rho_m$	Magnetic resistivity
$\Delta\rho$	Resistivity variation
$\rho_{tot}$	Total resistivity
$\sigma$	Conductivity
$\lambda_s$	Interface spin-scattering length

$\lambda_1$	Mean free path of sputtered atoms
AMR	Anisotropic magnetoresistance
AP	Antiparallel
AF	Antiferromagnetic
a	Radius of sphere
APCVD	Atmospheric pressure chemical vapor deposition
at%	Atomic percent
B	Magnetic induction
CIP	Current in plane
CPP	Current perpendicular to the plane
CMR	Colossal magnetoresistance
CVD	Chemical Vapor Deposition
d	Lattice spacing
DC	Direct Current
e	Charge of electron
EDX	Energy Dispersive X-ray
F	Ferromagnetic
$\bar{F}$	Force
GMR	Giant Magnetoresistance
$\vec{H}$	Magnetic field strength
HBT	Hetrojunction bipolar transition
HEMET	High electron mobility transistor

LSI	Large Scale Integration
$L_{SF}$	Spin-diffusion length
MBE	Molecular beam epitaxy
MESFET	Metal semiconductor field effect transistor
MOCVD	Metalorganic chemical vapor deposition
MR	Magnetoresistance
OMR	Ordinary magnetoresistance
PVD	Physical Vapor Deposition
PECVD	Plasma Enhanced chemical vapor deposition
$R_0$	Resistance at zero field
$R_H$	Resistance at applied magnetic field
RF	Radio Frequency
$R_{max}$	Maximum resistivity
SAW	Surface acoustic wave
SEM	Scanning Electron Microscopy
T	Tesla
$T_c$	Crystallization temperature
$T_{ept}$	Epitaxial temperature
$T_s$	Substrate temperature
TMR	Tunneling magnetoresistance
$T_A$	Annealing temperature
$t_F$	Ferromagnetic thickness
$t_N$	Non ferromagnetic thickness (normal thickness).

$v$	Velocity of electron
$V_{\text{scat}}$	Scattering potential
$V_{\text{cl}}$	Cluster volume fractions
$V_c$	Corrosion potential (unit cell volume)
W	Watt
XRD	X-Ray Diffraction

## **CHAPTER I**

### **INTRODUCTION**

Thin film is a deposition of atoms to form thin layer on a substrate, their thickness is typically less than several microns. The formation of thin films on a substrate by deposition is basically a phase change phenomenon involving nucleation and growth with the constraint of the substrate. There are important variables that should be controlled in a deposition process (Glang, 1970, Poate, et al, 1978 and Smith, 1995) such as

- a) Vacuum pressure
- b) Deposition rate
- c) Substrate material (structure)
- d) Substrate temperature
- e) Deposition atmosphere

The thin film process comprises of three elementary stages includes

- a) Production of the appropriate atomic, molecular, or ionic species
- b) Transport of the species to the substrate through a medium

c) Condensation on the substrate, either directly or through a chemical reaction to form a solid film

The starting materials in the form of gas, liquid, or solid are decomposed into various fragments of neutral or ions in the form of atoms, molecules, clusters or powders, by the external powers (Suzui, et al, 1998)

The crystalline properties of the deposited films are controlled by the selection of the substrate materials and the substrate temperature

The amorphous thin films are prepared on a glass and /or ceramic substrate at substrate temperature below the crystallization temperatures of the thin films Polycrystalline films are prepared on a glass and/ or ceramic substrates at the substrate temperatures above the crystallization temperature Single crystalline films are prepared on a single crystal substrate due to the epitaxial growth process and, in general, they are epitaxially grown on a single crystal substrate at the substrate temperature above the epitaxial temperature Table 1 lists the basic process of the deposition of the thin films